

REPLACEMENT SHEET

Sunlight

Sunlight

Sunlight

Sunlight

a-Si:H p-layer Ts=70°C

a-Si:H p-layer Ts=70°C

a-Si:H p-layer Ts=140°C

a-Si:H p-layer Ts=70°C
a-Si:H p-layer Ts=140°C

a-Si:H i-layer
 $E_g=1.8\text{ eV}$

a-SiGe:H i-layer
 $E_g=1.6\text{ eV}$

a-SiGe:H i-layer
 $E_g=1.6\text{ eV}$

a-SiGe:H i-layer
 $E_g=1.6\text{ eV}$

a-Si:H n-layer

a-Si:H n-layer

a-Si:H n-layer

a-Si:H n-layer

Fig. 1b

Fig. 2b

Fig. 3b

Fig. 4b

REPLACEMENT SHEET

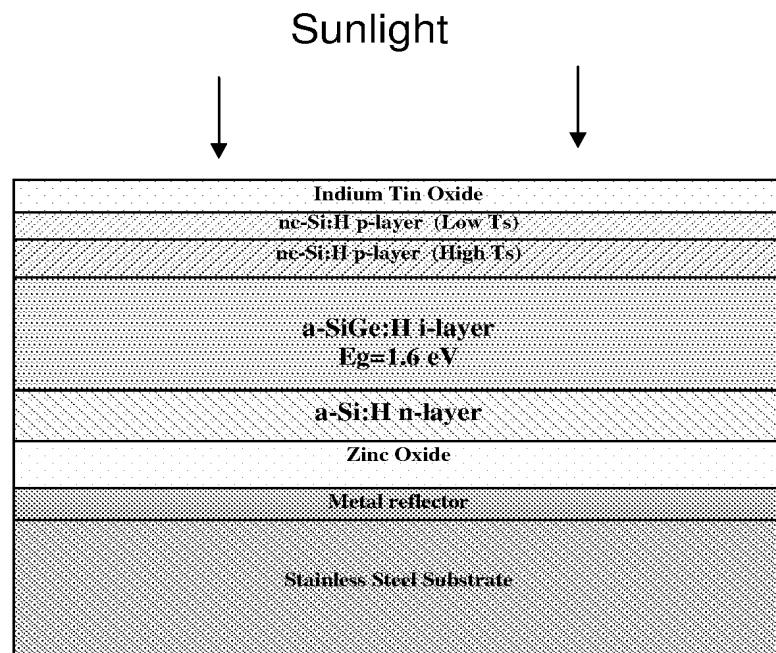


Fig. 5b